

## 产品概览

### NTMFS6H801N: 单 N 沟道，功率 MOSFET，80V，153A，2.8mΩ

欲看完整文档，请参阅数据表。

适用于紧凑和高效设计的商用功率 MOSFET，安装在 5x6mm 扁平引线封装中且具有较高的热性能。

#### 特性

- Small Footprint (5x6 mm)
- Low RDS(on)
- Low QG and Capacitance
- RoHS Compliant

#### 应用

- Switching power supplies
- Power switches (High Side Driver, Low Side Driver, H-Bridges etc.)
- 48V systems
- Battery management and protection

#### 优势

- Compact Design
- Minimize Conduction Losses
- Minimize Driver Losses

#### 终端产品

- Motor Control
- DC/DC converter
- Load Switch
- Synchronous Rectification
- Battery Packs and ESS

### 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V <sub>DSS</sub> (BR) Min (V)	V <sub>GS</sub> Max (V)	V <sub>GS(th)</sub> Max (V)	I <sub>D</sub> Max (A)	P <sub>D</sub> Max (W)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 2.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 4.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 10 V (mΩ)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 4.5 V (nC)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 10 V (nC)	C <sub>iss</sub> Typ (pF)	Package Type
NTMFS6H801NT1G	0.8666	Pb-free Halide free	Active	N-Channel	Single	80	20	4	203	3.8	-	-	2.1	-	85	5530	SO-8FL / DFN-5

欲了解更多信息，请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

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